

OPA6318

Orange LED Chip

GaAsP / GaP

1. Material Substrate GaP (N Type)
Epitaxial Layer GaAsP (P/N Type)

2. Electrode N (Cathode) Side Gold Alloy
P (Anode) Side Gold Alloy

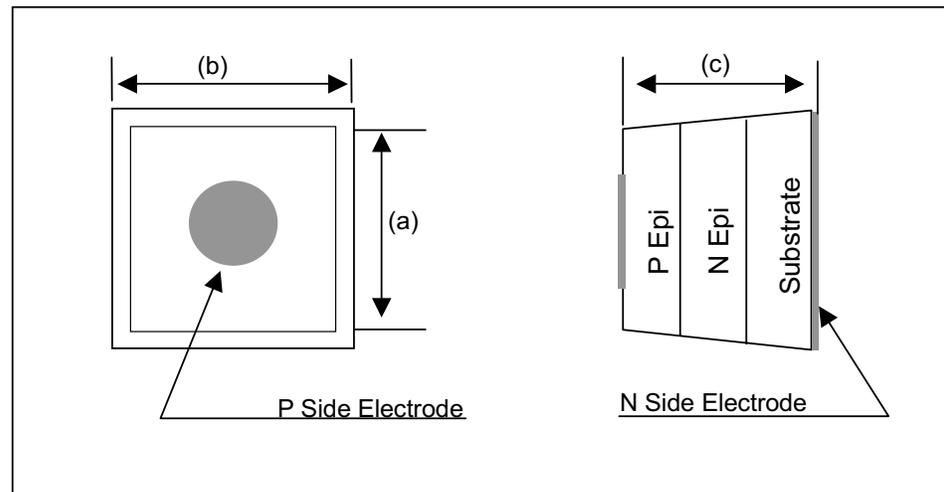
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	$I_F=1\text{mA}$
	$V_{F(2)}$		2.1	2.5	V	$I_F=20\text{mA}$
Reverse Voltage	V_R	6.0			V	$I_R=10\mu\text{A}$
Brightness	I_V	100	200		mcd	$I_F=20\text{mA}$
Wavelength	Hue		630		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		40		nm	$I_F=20\text{mA}$

※ Note: Assembled into T1^{3/4} plastic package.

4. Mechanical Data

- (a) Emission Area ----- 8mil × 8mil
- (b) Bottom Area ----- 10mil × 10mil
- (c) Chip Thickness ----- 10mil



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